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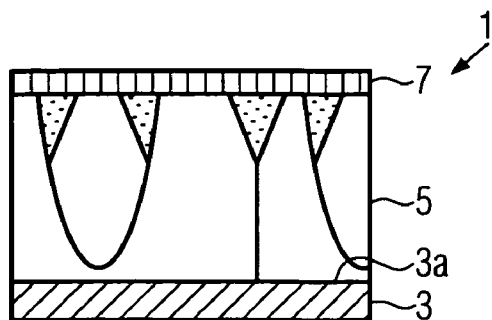
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(54) Title: A METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE

FIG. 1e



(57) Abstract: The present invention relates to a method for fabricating a semiconductor structure comprising a semiconductor layer (5) and a metallic layer (7), to improve the breakdown voltage properties of the device and reduce leakage currents, the method comprises the steps of: a) providing a semiconductor layer comprising defects and/or dislocations; b) removing material at one or more locations of the defects and/or dislocations thereby forming pits (13a-13d) in the semiconductor layer, c) passivating the pits (13a-13d), and c) providing the metallic layer (7) over the semiconductor layer (5). The invention also relates to a corresponding semiconductor structure.